

Approved
Plan 5/17/05

IN THE SPECIFICATION

Please replace the following paragraph beginning at page 23 line 25 and ending at page 24, line 11 with the following rewritten paragraph:

-- The control voltage V_c and the bias voltage ~~voltages V_{b1} and V_{b2}~~ are all set to above the ground potential. Furthermore, the bias voltage V_{b1} is set to a value not less than the gate threshold voltage of the FET 111. On the other hand, the bias voltage V_{b2} is set to a value not less than the gate threshold voltage of the FET 121. Setting examples and setting methods of these voltages will be described later in detail. Hereby, it becomes possible for the switching device 10 to operate only by a positive power supply. In the present embodiment, the control voltage V_c is settable in a range from about 0 V to about 5 V, and the bias voltages V_{b1} and V_{b2} are settable in a range from about 0 V to about 3 V. Furthermore, if the FET 121 is implemented by a FET that has high resistance to voltage, this makes it possible to increase the value of the bias voltage V_{b2} up to about 3.5 V. --